



High-Voltage Switching Applications

Applications

· Power supplies, relay derivers, lamp drivers.

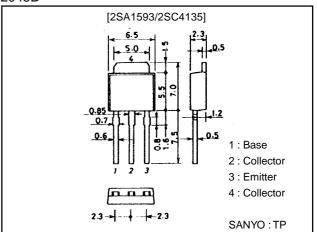
Features

- · Adoption of FBET, MBIT processes.
- · High breakdown voltage and large current capacity.
- · Fast switching speed.
- · Small and slim package permitting 2SA1593/ 2SC4135-applied sets to be made more compact.

Package Dimensions

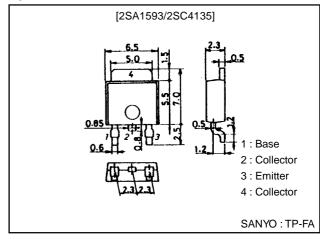
unit:mm

2045B



unit:mm

2044B



(): 2SA1593

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(–)120	V
Collector-to-Emitter Voltage	VCEO		(-)100	V
Emitter-to-Base Voltage	V _{EBO}		(–)6	V
Collector Current	IC		(-)2	Α
Collector Current (Pulse)	I _{CP}		(–)3	Α
Collector Dissipation	PC		1	W
		Tc=25°C	15	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

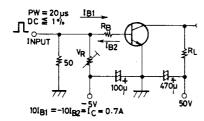
^{* :} The 2SA1593/2SC4135 are classified by 100mA h_{FE} as follows :

	100	R	200	140	S	280	200	Т	400
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Electrical Characteristics at Ta = 25°C

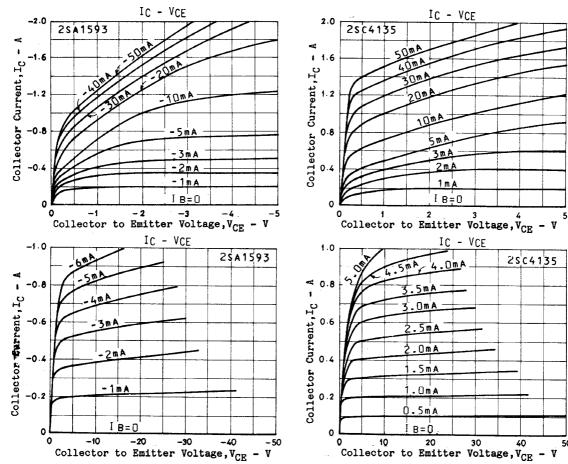
Parameter	Symbol	Conditions		Ratings		
Falametei	Symbol	Conditions		typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =(-)100V, I _E =0			(-)100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0			(–)100	nA
DC Current Gain	h _{FE}	V _{CE} =(-)5V, I _C =(-)100mA	100*		400*	
Gain-Bandwidth Product	fT	V _{CE} =(-)10V, I _C =(-)100mA		120		MHz
Output Capacitance	C _{ob}	V _{CB} =(-)10V, f=1MHz		(25)		pF
				16		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)1A, I _B =(-)100mA		(-0.22)	(-0.6)	V
				0.13	0.4	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)1A, I _B =(-)100mA		(-)0.85	(-)1.2	V
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =(-)10μΑ, I _E =0	(-)120			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(-)1mA, R _{BE} =∞	(-)100			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =(-)10μΑ, I _C =0	(-)6			V
Turn-ON Time	ton	See specified Test Circuit		(80)		ns
				80		ns
Storage Time	t _{stg}	See specified Test Circuit		(750)		ns
				1000		ns
Fall Time	t _f	See specified Test Circuit		(40)		ns
				50		ns

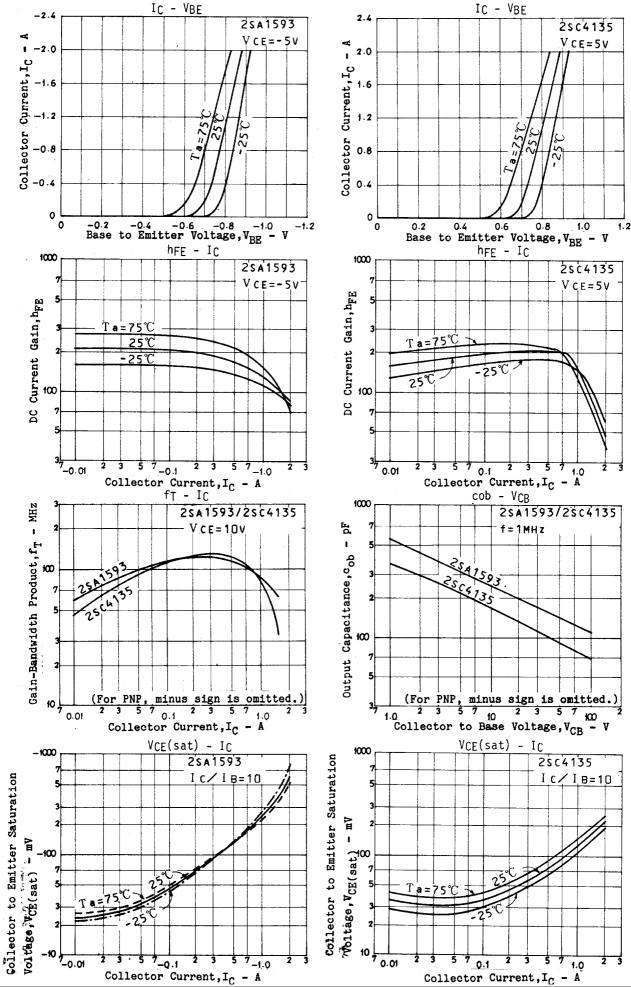
Switching Time Test Circuit



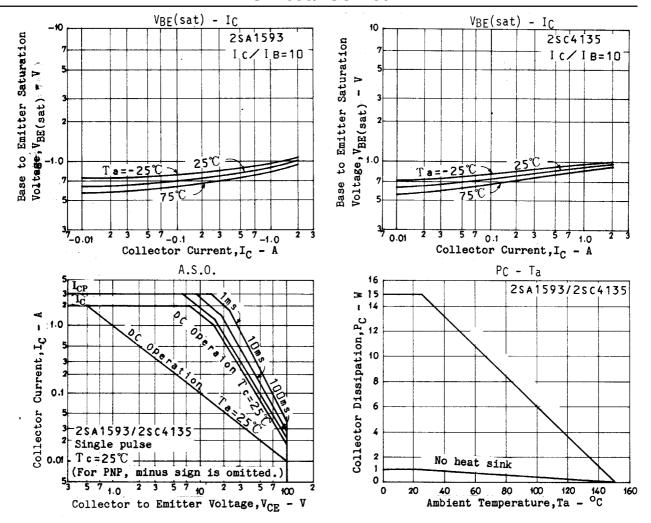
Unit (resistance $:\Omega$, capacitance :F)

(For PNP, the polarity is reversed.)





2SA1593/2SC4135



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